

Notice of References Cited	Application/Control No. 10/572,680	Applicant(s)/Patent Under Reexamination TOMOZAWA ET AL.	
	Examiner Hoang-Quan Ho	Art Unit 2818	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0010994	01-2003	Chen et al.	257/99
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
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	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Chen et al. Microstructural investigation of oxidized Ni/Au ohmic contact to p-type GaN. Oct. 1, 1999. Journal of Applied Physics. Vol. 86, No. 7. Pgs. 3826 - 3832.
	V	Sheu et al. The effect of thermal annealing on the Ni/Au contact of p-type GaN. Mar. 15, 1998. Journal of Applied Physics. Vol. 83, No. 6. Pgs. 3172 - 3175.
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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